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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details	
Product Status	Obsolete
Core Processor	ARM9®
Core Size	16/32-Bit
Speed	96MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, Microwire, SPI, SSI, SSP, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, Motor Control PWM, POR, PWM, WDT
Number of I/O	80
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 2V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str912faz46h6

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1 Description

STR91xFA is a series of ARM[®]-powered microcontrollers which combines a 16/32-bit ARM966E-S RISC processor core, dual-bank Flash memory, large SRAM for data or code, and a rich peripheral set to form an ideal embedded controller for a wide variety of applications such as point-of-sale terminals, industrial automation, security and surveillance, vending machines, communication gateways, serial protocol conversion, and medical equipment. The ARM966E-S core can perform single-cycle DSP instructions, good for speech processing, audio algorithms, and low-end imaging.

3 Functional overview

3.1 System-in-a-package (SiP)

The STR91xFA is a SiP device, comprised of two stacked die. One die is the ARM966E-S CPU with peripheral interfaces and analog functions, and the other die is the burst Flash. The two die are connected to each other by a custom high-speed 32-bit burst memory interface and a serial JTAG test/programming interface.

3.2 Package choice

STR91xFA devices are available in 128-pin (14 x 14 mm) and 80-pin (12 x 12 mm) LQFP and LFBGA144 (10 x 10 mm) packages. Refer to [Table 2: Device summary on page 11](#) for a list of available peripherals for each of the package choices.

3.3 ARM966E-S CPU core

The ARM966E-S core inherently has separate instruction and data memory interfaces (Harvard architecture), allowing the CPU to simultaneously fetch an instruction, and read or write a data item through two Tightly-Coupled Memory (TCM) interfaces as shown in [Figure 1](#). The result is streamlined CPU Load and Store operations and a significant reduction in cycle count per instruction. In addition to this, a 5-stage pipeline is used to increase the amount of operational parallelism, giving the most performance out of each clock cycle.

Ten DSP-enhanced instruction extensions are supported by this core, including single-cycle execution of 32x16 Multiply-Accumulate, saturating addition/subtraction, and count leading-zeros.

The ARM966E-S core is binary compatible with 32-bit ARM7 code and 16-bit Thumb[®] code.

3.4 Burst Flash memory interface

A burst Flash memory interface ([Figure 1](#)) has been integrated into the Instruction TCM (I-TCM) path of the ARM966E-S core. Also in this path is an 8-instruction Pre-Fetch Queue (PFQ) and a 15-entry Branch Cache (BC), enabling the ARM966E-S core to perform up to 96 MIPS while executing code directly from Flash memory. This architecture provides high performance levels without a costly instruction SRAM, instruction cache, or external SDRAM. Eliminating the instruction cache also means interrupt latency is reduced and code execution becomes more deterministic.

3.4.1 Pre-fetch queue (PFQ)

As the CPU core accesses sequential instructions through the I-TCM, the PFQ always looks ahead and will pre-fetch instructions, taking advantage any idle bus cycles due to variable length instructions. The PFQ will fetch 32-bits at a time from the burst Flash memory at a rate of up to 96 MHz.

3.4.2 Branch cache (BC)

When instruction addresses are not sequential, such as a program branch situation, the PFQ would have to flush and reload which would cause the CPU to stall if no BC were present. Before reloading, the PFQ checks the BC to see if it contains the desired target branch address. The BC contains up to fifteen of the most recently taken branch addresses and the first eight instructions associated with each of these branches. This check is extremely fast, checking all fifteen BC entries simultaneously for a branch address match (cache hit). If there is a hit, the BC rapidly supplies the instruction and reduces the CPU stall. This gives the PFQ time to start pre-fetching again while the CPU consumes these eight instructions from the BC. The advantage here is that program loops (very common with embedded control applications) run very fast if the address of the loops are contained in the BC.

In addition, there is a 16th branch cache entry that is dedicated to the Vectored Interrupt Controller (VIC) to further reduce interrupt latency by eliminating the stall latency typically imposed by fetching the instruction that reads the interrupt vector address from the VIC.

3.4.3 Management of literals

Typical ARM architecture and compilers do not place literals (data constants) sequentially in Flash memory with the instructions that use them, but instead the literals are placed at some other address which looks like a program branch from the PFQ's point of view. The STR91xFA implementation of the ARM966E-S core has special circuitry to prevent flushing the PFQ when literals are encountered in program flow to keep performance at a maximum.

3.9 Vectored interrupt controller (VIC)

Interrupt management in the STR91xFA is implemented from daisy-chaining two standard ARM VIC units. This combined VIC has 32 prioritized interrupt request channels and generates two interrupt output signals to the CPU. The output signals are FIQ and IRQ, with FIQ having higher priority.

3.9.1 FIQ handling

FIQ (Fast Interrupt reQuest) is the only non-vectored interrupt and the CPU can execute an Interrupt Service Routine (ISR) directly without having to determine/prioritize the interrupt source, minimizing ISR latency. Typically only one interrupt source is assigned to FIQ. An FIQ interrupt has its own set of banked registers to minimize the time to make a context switch. Any of the 32 interrupt request input signals coming into the VIC can be assigned to FIQ.

3.9.2 IRQ handling

IRQ is a vectored interrupt and is the logical OR of all 32 interrupt request signals coming into the 32 IRQ channels. Priority of individual vectored interrupt requests is determined by hardware (IRQ channel Intr 0 is highest priority, IRQ channel Intr 31 is lowest).

However, inside the same VIC (primary or secondary VIC), CPU firmware may re-assign individual interrupt sources to individual hardware IRQ channels, meaning that firmware can effectively change interrupt priority levels as needed within the same VIC (from priority 0 to priority 16).

Note: VIC0 (primary VIC) interrupts always have higher priority than VIC1 (secondary VIC) interrupts

When the IRQ signal is activated by an interrupt request, VIC hardware will resolve the IRQ interrupt priority, then the ISR reads the VIC to determine both the interrupt source and the vector address to jump to the service code.

The STR91xFA has a feature to reduce ISR response time for IRQ interrupts. Typically, it requires two memory accesses to read the interrupt vector address from the VIC, but the STR91xFA reduces this to a single access by adding a 16th entry in the instruction branch cache, dedicated for interrupts. This 16th cache entry always holds the instruction that reads the interrupt vector address from the VIC, eliminating one of the memory accesses typically required in traditional ARM implementations.

3.9.3 Interrupt sources

The 32 interrupt request signals coming into the VIC on 32 IRQ channels are from various sources; 5 from a wake-up unit and the remaining 27 come from internal sources on the STR91xFA such as on-chip peripherals, see [Table 6](#). Optionally, firmware may force an interrupt on any IRQ channel.

One of the 5 interrupt requests generated by the wake-up unit (IRQ25 in [Table 6](#)) is derived from the logical OR of all 32 inputs to the wake-up unit. Any of these 32 inputs may be used to wake up the CPU and cause an interrupt. These 32 inputs consist of 30 external interrupts on selected and enabled GPIO pins, plus the RTC interrupt, and the USB Resume interrupt.

5.2 Default pin functions

During and just after reset, all pins on ports 0-9 default to high-impedance input mode until CPU firmware assigns other functions to the pins. This initial input mode routes all pins on ports 0-9 to be read as GPIO inputs as shown in the “Default Pin Function” column of [Table 8](#). Simultaneously, certain port pin signals are also routed to other functional inputs as shown in the “Default Input Function” column of [Table 8](#), and these pin input functions will remain until CPU firmware makes other assignments. At any time, even after the CPU assigns pins to alternate functions, the CPU may always read the state of any pin on ports 0-9 as a GPIO input. CPU firmware may assign alternate functions to port pins as shown in columns “Alternate Input 1” or “Alternate Output 1, 2, 3” of [Table 8](#) by writing to control registers at run-time.

5.2.1 General notes on pin usage

- 1 *Since there are no internal or programmable pull-up resistors on ports 0-9, it is advised to pull down to ground, or pull up to VDDQ (using max. 47 K Ω resistors), all unused pins on port 0-9. Another solution is to use the GPIO control registers to configure the unused pins on ports 0-9 as output low level. The purpose of this is to reduce noise susceptibility, noise generation, and minimize power consumption*
- 2 *All pins on ports 0 - 9 are 5V tolerant*
- 3 *Pins on ports 0,1,2,4,5,7,8,9 have 4 mA drive and 4mA sink. Ports 3 and 6 have 8 mA drive and 8 mA sink.*
- 4 *For 8-bit non-muxed EMI operation: Port 8 is eight bits of data, ports 7 and 9 are 16 bits of address.*
- 5 *For 16-bit muxed EMI operation: Ports 8 and 9 are 16 bits of muxed address and data bits, port 7 is up to eight additional bits of high-order address*
- 6 *Signal polarity is programmable for interrupt request inputs, EMI_ALE, timer input capture inputs and output compare/PWM outputs, motor control tach and emergency stop inputs, and motor control phase outputs.*
- 7 *HiZ = High Impedance, V = Voltage Source, G = Ground, I/O = Input/Output*
- 8 *STR910FA devices do not support USB. On these devices USBDP and USBDN signals are "Not Used" (USBPN is not connected, USBDP must be pulled up by a 1.5K ohm resistor to VDDQ), and all functions named "USB" are not available.*
- 9 *STR910FA 128-pin and 144-ball devices do not support Ethernet. On these devices PHYCLK and all functions named "MII*" are not available.*

Figure 9. STR91xFA memory map

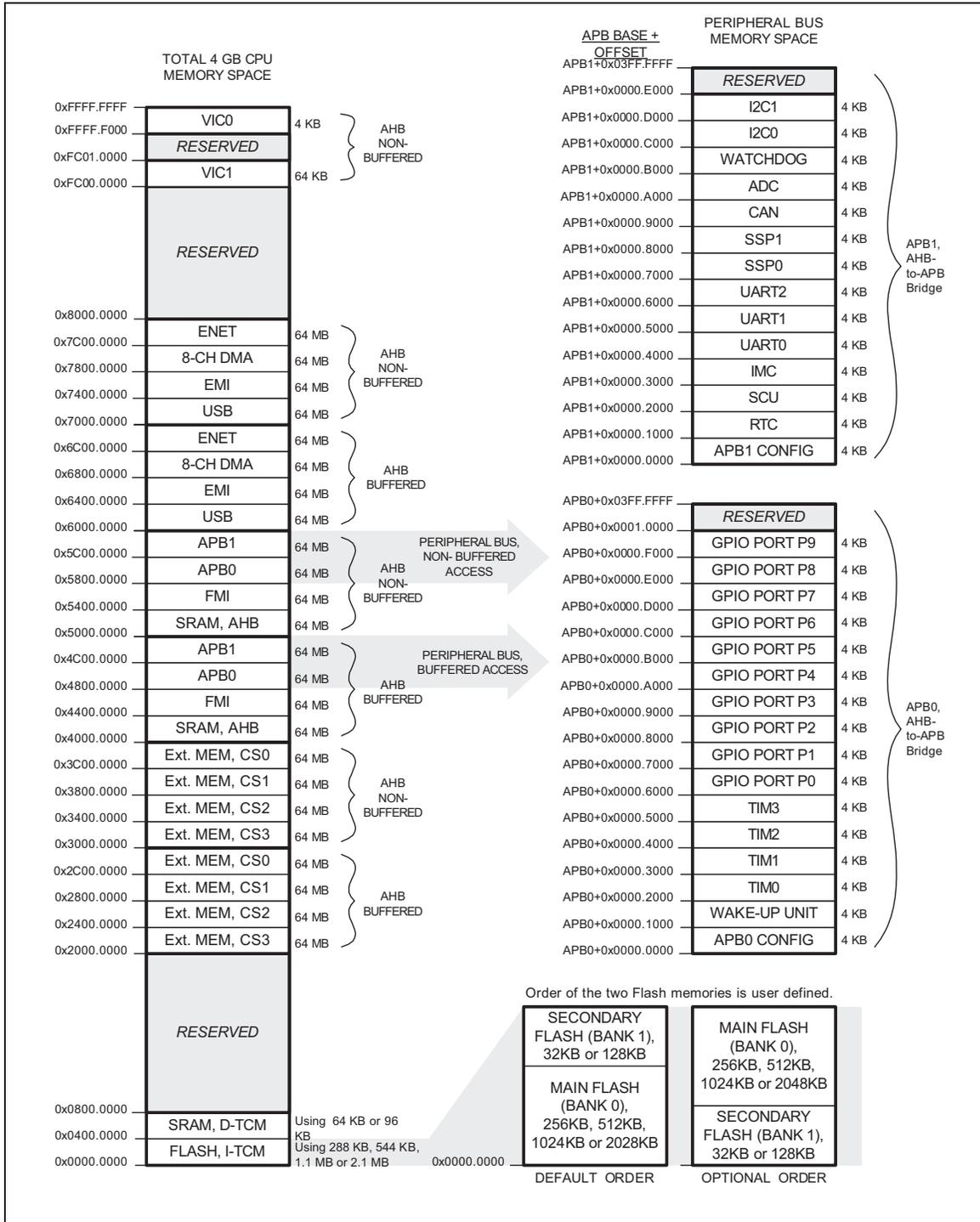


Table 25. Flash memory program/erase characteristics (Flash size = 1 MB / 2 MB)

Parameter		Test conditions	Value			Unit
			Typ ⁽¹⁾	Typ after 100K W/E cycles ⁽¹⁾	Max	
Bank erase	Primary bank (2 Mbytes)		32	36	46	s
	Primary bank (1 Mbytes)		16	18	23	s
	Secondary bank (128 Kbytes)		2.5	3	4	s
Sector erase	Of primary bank (64 Kbytes)		1300	1400	1800	ms
	Of secondary bank (16 Kbytes)		500	600	850	ms
Bank program	Primary bank (2 Mbytes)		15	20	22	s
	Primary bank (1 Mbytes)		7.5	10	11	s
	Secondary bank (128 Kbytes)		1060	1140	1380	ms
Sector program	Of primary bank (64 Kbytes)		500	520	640	ms
	Of secondary bank (16 Kbytes)		120	130	160	ms
Word program		Half word (16 bits)	8	9	11	µs

1. $V_{DD} = 1.8\text{ V}$, $V_{DDQ} = 3.3\text{ V}$, $T_A = 25^\circ\text{C}$.

Table 26. Flash memory endurance

Parameter	Test conditions	Value			Unit
		Min	Typ	Max	
Program/erase cycles	Per word	100K			cycles
Data retention		20			years

7.9 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

7.9.1 Functional EMS (electro magnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electro magnetic events until a failure occurs (indicated by the LEDs).

- **ESD:** Electro-Static Discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} , V_{DDQ} and V_{SS} through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Table 27. EMS data

Symbol	Parameter	Conditions	Severity/ Criteria ⁽¹⁾	Unit
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 1.8\text{ V}$, $V_{DDQ} = 3.3\text{ V}$, $T_A = +25\text{ °C}$, $f_{OSC}/f_{CPUCLK} = 4\text{ MHz}/96\text{ MHz PLL}$	1B	kV
V_{FFTB}	Fast transient voltage burst limits to be applied through 100pF on V_{DD} and V_{DDQ} pins to induce a functional disturbance	$V_{DD}=1.8\text{ V}$, $V_{DDQ} = 3.3\text{ V}$, $T_A = +25\text{ °C}$, $f_{OSC}/f_{CPUCLK} = 4\text{ MHz}/96\text{ MHz PLL}$ conforms to IEC 1000-4-4	4A	

1. Data based on characterization results, not tested in production.

7.9.2 Electro magnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 28. EMI data

Symbol	Parameter	Conditions	Monitored Frequency Band	Max vs. [f _{osc} /f _{CPUCLK}]		Unit
				24 MHz / 48 MHz ⁽¹⁾	24 MHz / 96 MHz ⁽¹⁾	
S _{EMI}	Peak level	V _{DDQ} = 3.3 V, V _{DD} = 1.8 V, T _A = +25 °C, LQFP128 package ⁽²⁾ conforming to SAE J 1752/3	0.1 MHz to 30 MHz	14	10	dB μ V
			30 MHz to 130 MHz	18	19	
			130 MHz to 1GHz	18	22	
			SAE EMI Level	4	4	-

1. Data based on characterization results, not tested in production.

2. BGA and LQFP devices have similar EMI characteristics.

7.9.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

7.9.4 Electro-static discharge (ESD)

Electro-Static Discharges (3 positive then 3 negative pulses separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 29. ESD data

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electro-static discharge voltage (Human Body Model)	T _A = +25°C conforming to JESD22-A114	2	+/-2000	V
V _{ESD(CDM)}	Electro-static discharge voltage (Charged Device Model)	T _A = +25°C conforming to JESD22-C101	II	1000	

1. Data based on characterization results, not tested in production.

7.9.5 Static latch-up

Two complementary static tests are required on 10 parts to assess the latch-up performance.

- A supply overvoltage (applied to each power supply pin) and
- A current injection (applied to each input, output and configurable I/O pin) are performed on each sample.

This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

7.9.6 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

7.9.7 Electrical sensitivity

Table 30. Static latch-up data

Symbol	Parameter	Conditions	Class ⁽¹⁾
LU	Static latch-up class	T _A = +25 °C conforming to JESD78A	II class A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

Mux write

Figure 20. Mux write diagram

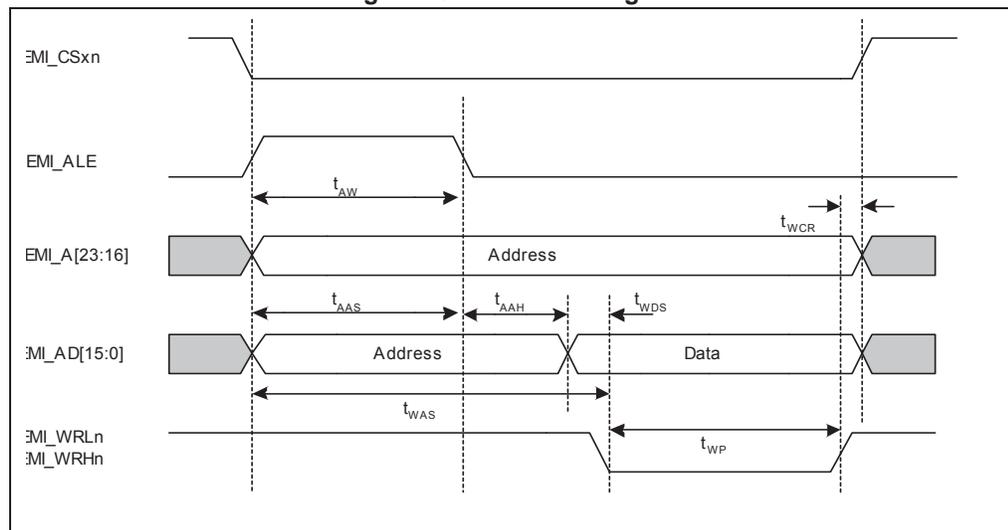


Table 35. Mux write times

Symbol	Parameter	Value	
		Min	Max
t_{WCR}	WRn to CSn inactive	$(t_{\text{BCLK}}/2) - 2\text{ns}$	$(t_{\text{BCLK}}/2) + 2\text{ns}$
t_{WAS}	Write address setup time	$(\text{WSTWEN} + 1/2) \times t_{\text{BCLK}} - 2.5\text{ ns}$	$(\text{WSTWEN} + 1/2) \times t_{\text{BCLK}} + 2\text{ ns}$
t_{WDS}	Write data setup time	$((\text{WSTWEN} - \text{ALE_LENGTH}) \times t_{\text{BCLK}}) - 2\text{ ns}$	$((\text{WSTWEN} - \text{ALE_LENGTH}) \times t_{\text{BCLK}}) + 1\text{ ns}$
t_{WP}	Write pulse width	$((\text{WSTWR} - \text{WSTWEN} + 1) \times t_{\text{BCLK}}) - 1\text{ ns}$	$((\text{WSTWR} - \text{WSTWEN} + 1) \times t_{\text{BCLK}}) + 1.5\text{ ns}$
t_{AW}	ALE pulse width	$(\text{ALE_LENGTH} \times t_{\text{BCLK}}) - 3.5\text{ ns}$	$(\text{ALE_LENGTH} \times t_{\text{BCLK}})$
t_{AAS}	Address to ALE setup time	$(\text{ALE_LENGTH} \times t_{\text{BCLK}}) - 3.5\text{ ns}$	$(\text{ALE_LENGTH} \times t_{\text{BCLK}})$
t_{AAH}	Address to ALE hold time	$(t_{\text{BCLK}}/2) - 1\text{ ns}$	$(t_{\text{BCLK}}/2) + 2\text{ ns}$

7.11.2 Synchronous mode

Sync burst write

Figure 23. Sync burst write diagram

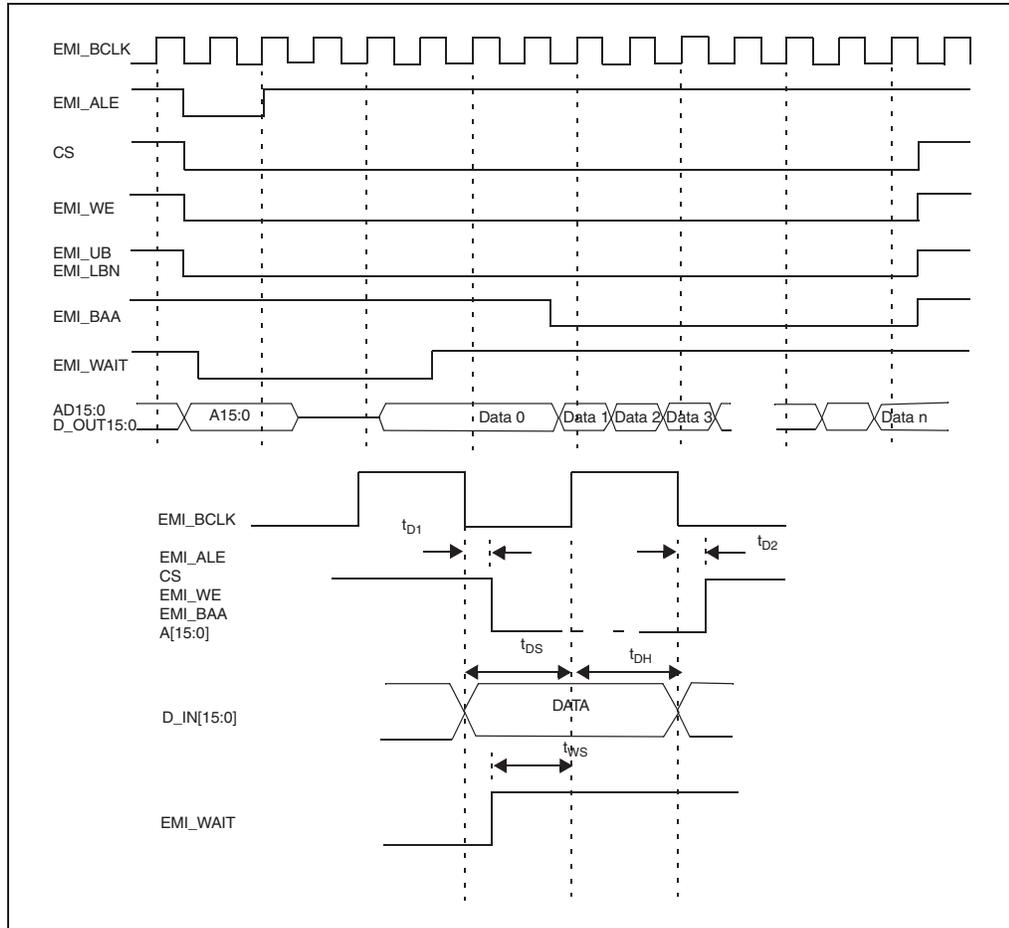


Table 38. Sync burst write times

Symbol	Parameter	Value	
		Min	Max
t_{D1BAA}	BAA t_{D1}	0	2 ns
t_{D2BAA}	BAA t_{D2}	0.5 ns	2.5 ns
t_{D1ALE}	ALE t_{D1}	1 ns	3.5 ns
t_{D2ALE}	ALE t_{D2}	$(t_{BCLK}/2) - 0.5$ ns	$(t_{BCLK}/2) + 3.5$ ns
t_{D1WR}	RD t_{D1}	0	2ns
t_{D2WR}	RD t_{D2}	0.5 ns	2.5 ns
t_{D1A}	Address t_{D1}	1.5 ns	4 ns
t_{D2A}	Address t_{D2}	2ns	4.5 ns
t_{D1CS}	CS t_{D1}	0.5ns	3 ns
t_{D2CS}	CS t_{D2}	1 ns	3.5 ns
t_{WS}	WAIT setup time	3 ns	6 ns
t_{DS}	Data setup time	$(t_{BCLK}/2) - 3.5$ ns	$(t_{BCLK}/2) + 0.5$ ns
t_{DH}	Data hold time	$(t_{BCLK}/2) - 1$ ns	$(t_{BCLK}/2) + 3.5$ ns

Sync burst read

Figure 24. Sync burst read diagram

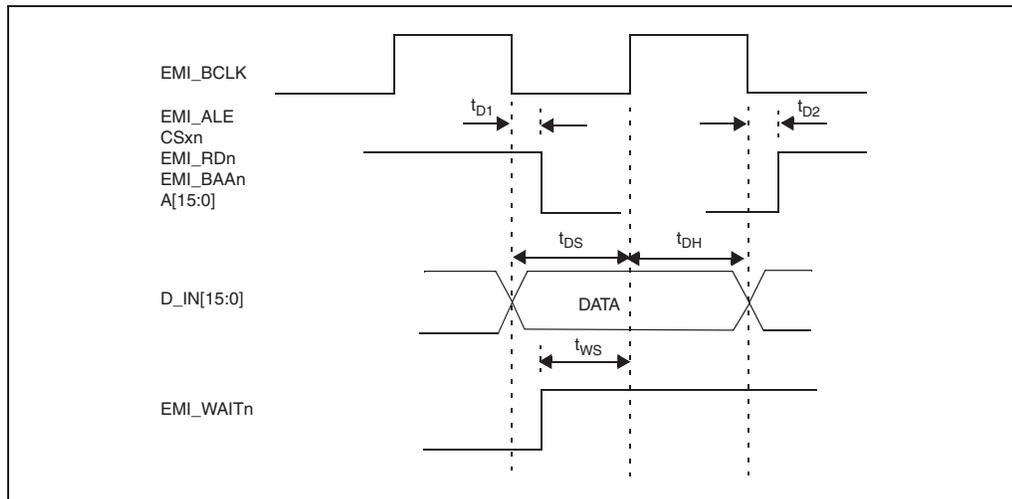


Table 39. Sync burst read times

Symbol	Parameter	Value	
		Min	Max
t _{D1BAA}	BAA t _{D1}	0 ns	2 ns
t _{D2BAA}	BAA t _{D2}	0.5 ns	2.5 ns
t _{D1ALE}	ALE t _{D1}	1 ns	3.5 ns
t _{D2ALE}	ALE t _{D2}	(t _{BCLK} /2)+0.5 ns	(t _{BCLK} /2)+3 ns
t _{D1RD}	RD t _{D1}	0	2 ns
t _{D2RD}	RD t _{D2}	0.5 ns	2.5 ns
t _{D1A}	Address t _{D1}	2 ns	4 ns
t _{D2A}	Address t _{D2}	2.5 ns	3.5 ns
t _{D1CS}	CS t _{D1}	0.5 ns	3 ns
t _{D2CS}	CS t _{D2}	1 ns	3.5 ns
t _{WS}	WAIT set up time	1 ns	4 ns
t _{DS}	Data setup time	4.5 ns	-
t _{DH}	Data hold time	0	-

Figure 31. SPI slave timing diagram with CPHA = 1

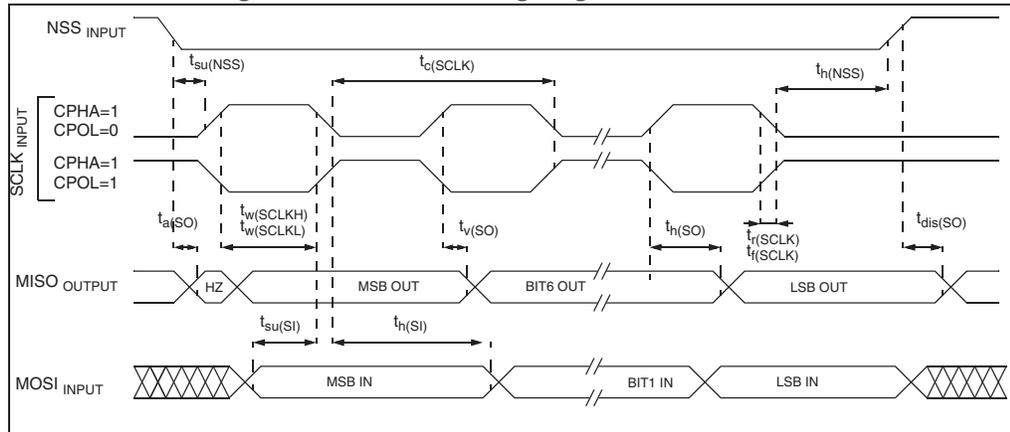
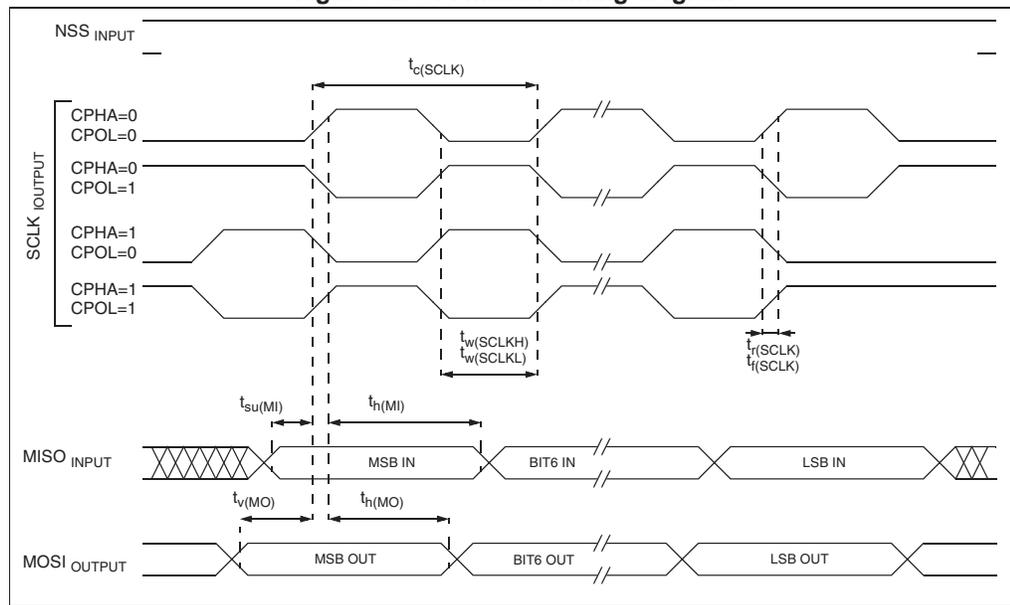


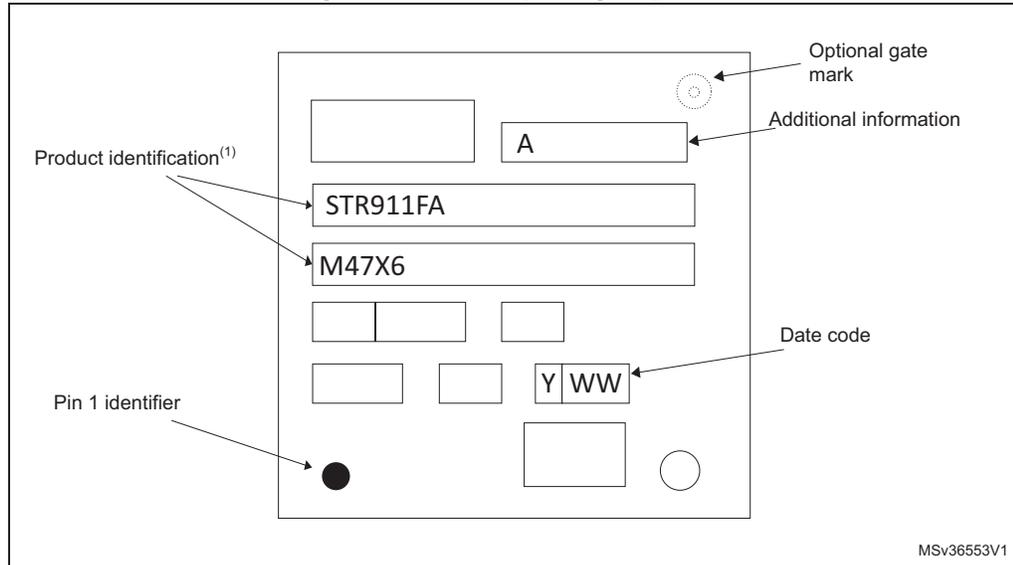
Figure 32. SPI master timing diagram



Marking of engineering samples for LQFP80

The following figure shows the engineering sample marking for the LQFP80 package. Only the information field containing the engineering sample marking is shown

Figure 42. LQFP80 package top view



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

9.1 ECOPACK

To meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions, and product status are available at www.st.com.

9.2 Thermal characteristics

The average chip-junction temperature, T_J must never exceed 125 °C.

The average chip-junction temperature, T_J , in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \quad (1)$$

Where:

- T_A is the ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),
- P_{INT} is the product of I_{DD} and V_{DD} , expressed in Watts. This is the Chip Internal Power.

$P_{I/O}$ represents the power dissipation on input and output pins;

Most of the time for the applications $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories. The worst case P_{INT} of the STR91xFA is 500 mW ($I_{DD} \times V_{DD}$, or 250 mA x 2.0 V).

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273 \text{ °C}) \quad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273 \text{ °C}) + \Theta_{JA} \times P_D^2 \quad (3)$$

Where:

- K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A .

Table 53. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP 80 - 12 x 12 mm / 0.5 mm pitch	41.5	°C/W
Θ_{JA}	Thermal resistance junction-ambient LQFP128 - 14 x 14 mm / 0.4 mm pitch	38	°C/W
Θ_{JA}	Thermal resistance junction-ambient LFBGA 144 - 10 x 10 x 1.7 mm	36.5	°C/W

Table 55. Document revision history

Date	Revision	Changes
02-Jul-2009	6	<p><i>Section 3.13.7: Tamper detection</i>: Removed information about "Normally Closed/Tamper Open mode".</p> <p><i>Table 31: I/O characteristics</i>: Updated V_{HYS} row.</p>
3-Mar-2015	7	<p>Updated <i>Figure 40: LQFP80 12 x 12 mm 80 pin low-profile quad flat package outline on page 95</i>, <i>Figure 43: LQFP128 14 x 14 mm 128 pin low-profile quad flat package outline on page 98</i> and <i>Figure 45: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package outline on page 101</i></p> <p>Updated <i>Table 50: LQFP80 12 x12 mm low-profile quad flat package mechanical data on page 96</i>, <i>Table 51: LQFP128 - 128-pin, 14 x 14 mm low-profile quad flat package mechanical data on page 99</i>, and <i>Table 52: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data on page 102</i></p> <p>Added <i>Figure 42: LQFP80 package top view on page 97</i>, <i>Figure 43: LQFP128 14 x 14 mm 128 pin low-profile quad flat package outline on page 98</i>, <i>Figure 44: LQFP128 package top view on page 100</i> and <i>Figure 45: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package outline on page 101</i></p>